

IN THE SPECIFICATION

Please amend the Title at page 1, lines 1-2 as follows:

SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING THE SAME
INCLUDING SILICIDED SOURCE AND DRAIN ELECTRODES

Please amend the paragraph at page 15, lines 31-34 as follows:

Likewise, by using Al or Cu, metal wiring can be formed through via-holes opened in the ~~insulating~~ insulating layer to the NiSi layer at a temperature not exceeding the critical temperature obtained by Fig. 6 or the expression (1).